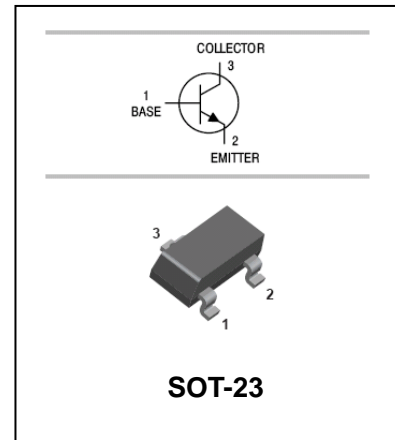


Silicon Epitaxial Planar Transistor

2SC2411

FEATURES

- Power dissipation: $P_{CM}=200\text{mW}$.
- High $I_{CM(\text{MAX.})}$, $I_{CM(\text{MAX.})}=0.5\text{mA}$.
- Low $V_{CE(\text{sat})}$.
- Complements the 2SA1036.



APPLICATIONS

- NPN Silicon Epitaxial Planar Transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC2411	CP/CQ/CR	SOT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	32	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to+150	$^\circ\text{C}$



Silicon Epitaxial Planar Transistor

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=100mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.4	V
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0$ $f=1MHz$		6.0		pF
Transition frequency	f_T	$V_{CE}=5V, I_C=-20mA$ $f=100MHz$		250		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	CP	CQ	CR

Silicon Epitaxial Planar Transistor

2SC2411

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

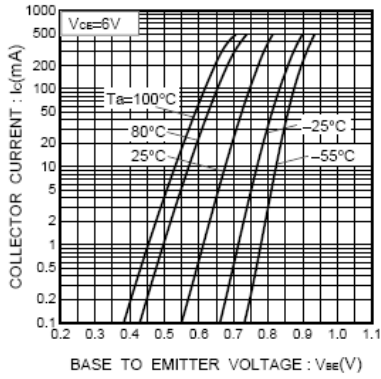


Fig.1 Grounded emitter propagation characteristics

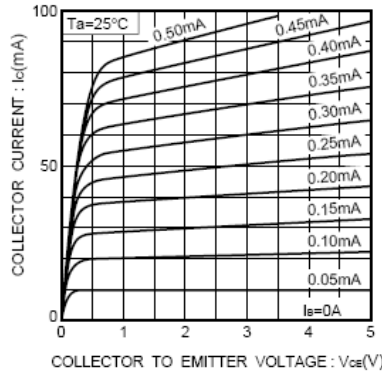


Fig.2 Grounded emitter output characteristics(I)

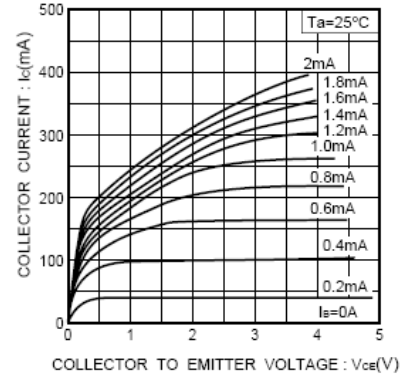


Fig.3 Grounded emitter output characteristics(II)

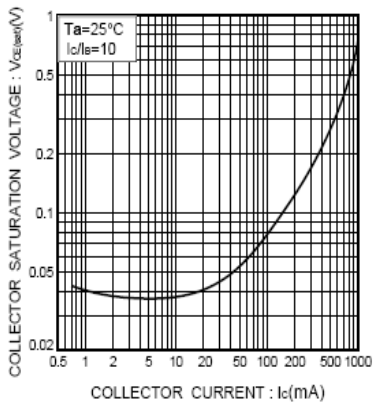


Fig.4 Collector-emitter saturation voltage vs. collector current

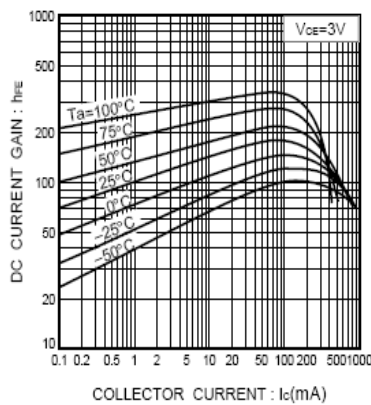


Fig.5 DC current gain vs. collector current

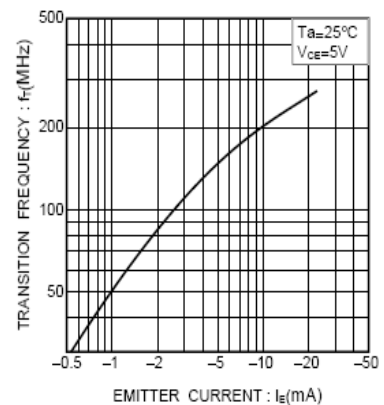


Fig.6 Gain bandwidth product vs. emitter current

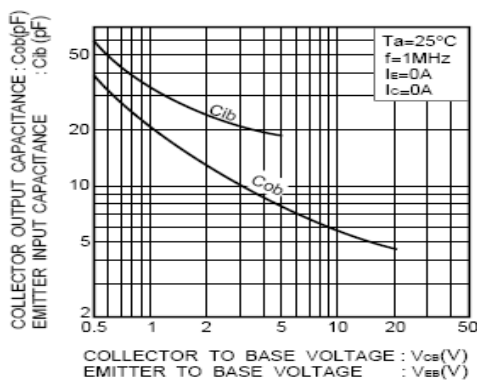


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Silicon Epitaxial Planar Transistor

2SC2411

PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC2411	SOT-23	3000/Tape&Reel